/ Descriptions

TO-252 N

N-CHANNEL MOSFET in a TO-252 Plastic Package.

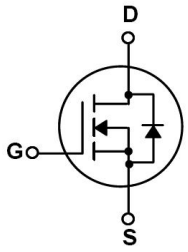
V_{DS}=100V I_D=60A

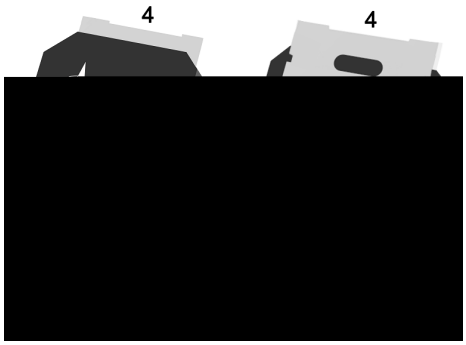
$R_{DS(ON)}$@10V ≤ 10mΩ(Typ.9mΩ)

$R_{DS(ON)}$@4.5V ≤ 15mΩ(Typ.11mΩ)

HF Product.

High Frequency Switching and Synchronous Rectification.





PIN1 G PIN 2 D PIN 3 S PIN 4 D

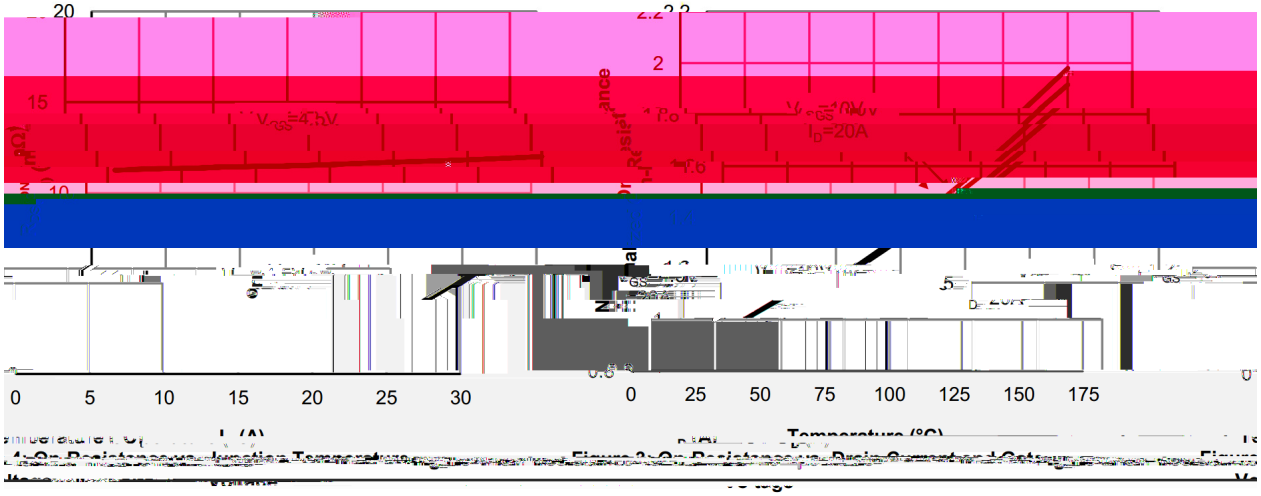
/ Marking

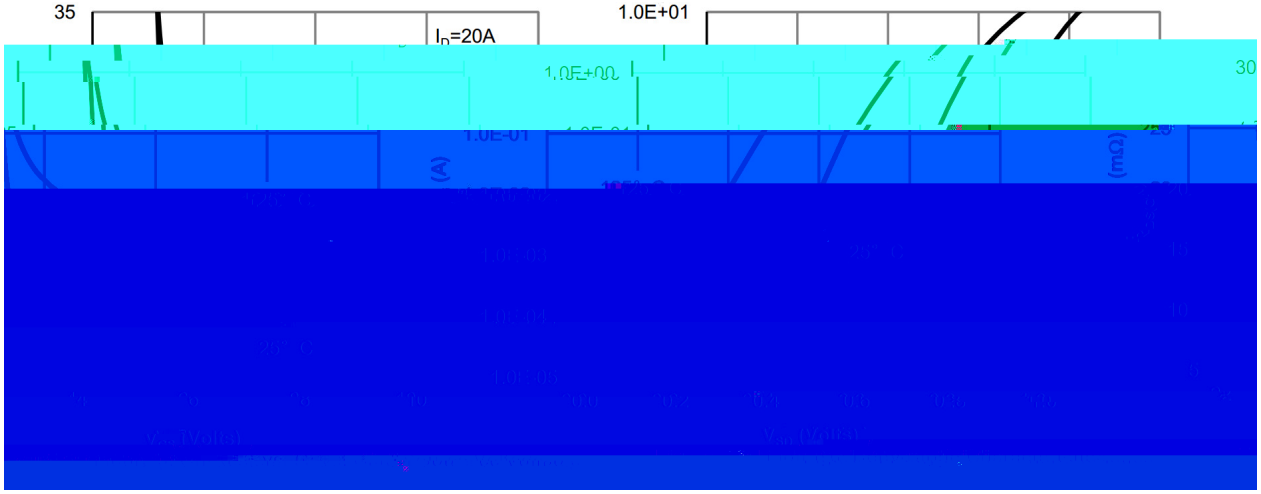
See Marking Instructions.

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	V_{GS}=10V V_{DS}=50V R_L=2.5Ω R_{GEN}=3Ω		8.7		ns
Turn-On Rise Time	t_r			3.5		
Turn-Off Delay Time	$t_{d(off)}$			25		
Turn-Off Fall Time	t_f			4.2		

/ Electrical Characteristic Curve







/ Electrical Characteristic Curve

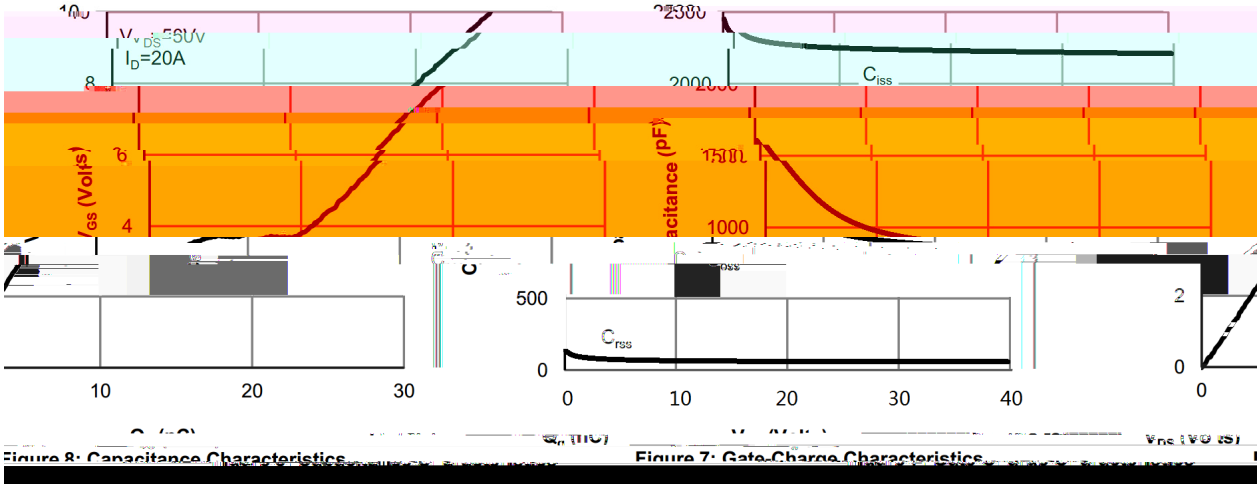
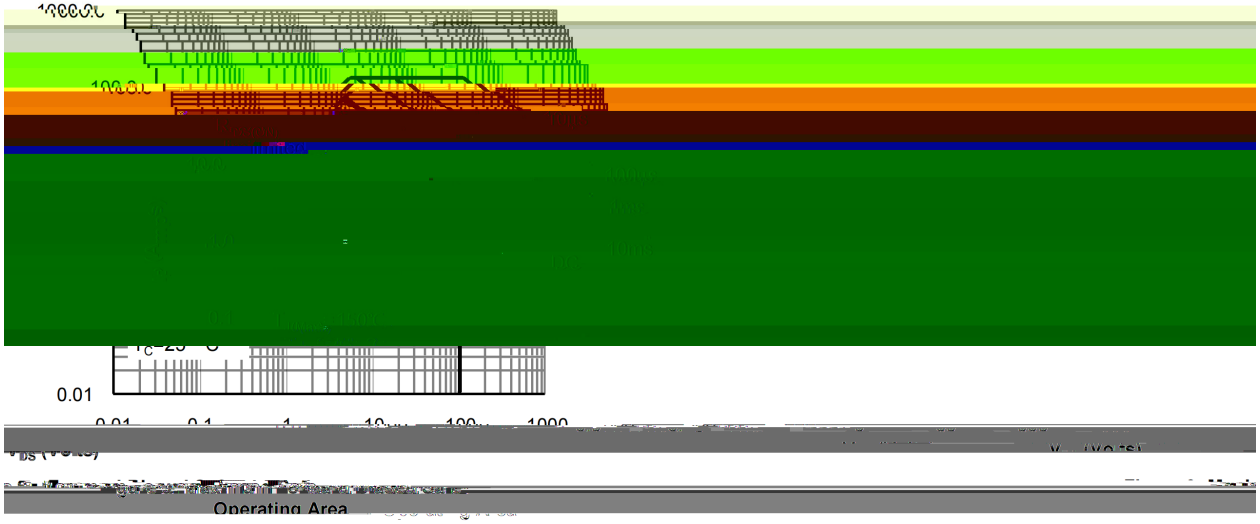


Figure 8: Capacitance Characteristics

Figure 7: Gate-Charge Characteristics



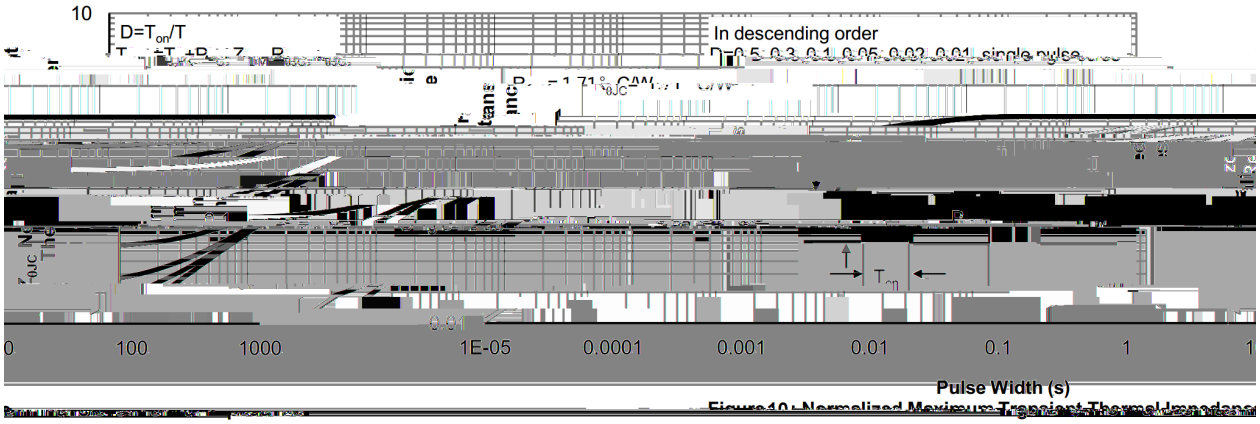
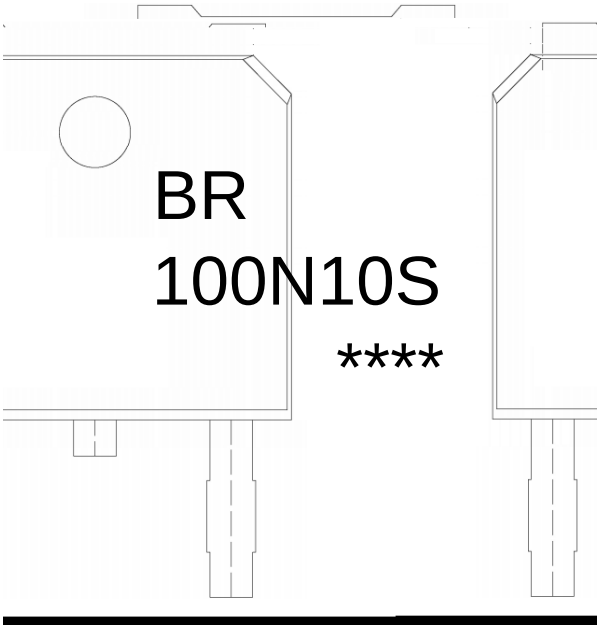


Figure 10: Normalized Maximum Transient Thermal Impedance

/ Package Dimensions



/ Marking Instructions



BR

100N10S

Note:

BR:	Company Code
100N10S:	Product Type Code
****:	Lot No. Code, code change with Lot No

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)

Note:

1 150 180 60 90sec;

2 245 5 5 0.5sec;

3 2 10 /sec.

1.Preheating:150~180 , Time:60~90sec.

2.Peak Temp.:245 5 , Duration:5 0.5sec.

3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

260 5 10 1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL